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August 2016

# MCT6, MCT61, MCT62 8-Pin Dual Channel Phototransistor Optocouplers

### Features

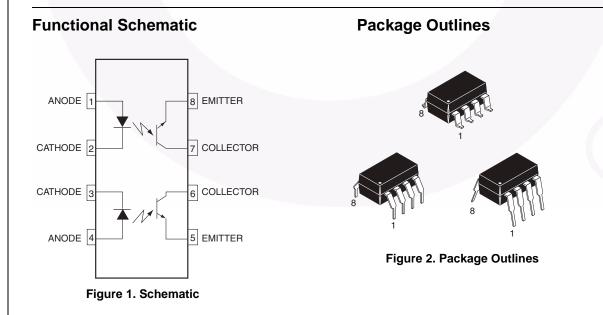
- Two Isolated Channels Per Package
  - Safety and Regulatory Approvals:
  - UL1577, 5,000 VAC<sub>RMS</sub> for 1 Minute
  - DIN-EN/IEC60747-5-5, 890 V Peak Working Insulation Voltage

# Applications

- AC line/digital logic isolate high voltage transients
- Digital logic/digital logic eliminate spurious grounds
- Digital logic/AC triac control isolate high voltage
- transients
- Twisted pair line receiver eliminate ground loop
- feedthrough
- Telephone/telegraph line receiver isolate high
- voltage transients
- High frequency power supply feedback control –
- maintain floating grounds and transients
- · Relay contact monitor isolate floating grounds and
- transients
- Power supply monitor isolate transients

## Description

The general purpose optocouplers, MCT6, MCT61, and MCT62, have two isolated channels in a standard plastic 8-pin dual-in-line (DIP) package for density applications. Each channel consists of a gallium arsenide infrared emitting diode driving a NPN silicon planar phototransistor. For four channel applications, two packages fit into a standard 16-pin DIP socket.



### Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE	< 150 V <sub>RMS</sub>	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–IV
Climatic Classification		55/115/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test with t <sub>m</sub> = 10 s, Partial Discharge < 5 pC	1424	V <sub>peak</sub>
V <sub>PR</sub>	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$ , 100% Production Test with t <sub>m</sub> = 1 s, Partial Discharge < 5 pC	1668	V <sub>peak</sub>
VIORM	Maximum Working Insulation Voltage	890	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	8000	V <sub>peak</sub>
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
Τ <sub>S</sub>	Case Temperature <sup>(1)</sup>	175	°C
I <sub>S,INPUT</sub>	Input Current <sup>(1)</sup>	60	mA
S,OUTPUT	Output Power <sup>(1)</sup>	150	mW
R <sub>IO</sub>	Insulation Resistance at T <sub>S</sub> , V <sub>IO</sub> = 500 V <sup>(1)</sup>	> 10 <sup>9</sup>	Ω

#### Note:

1. Safety limit values - maximum values allowed in the event of a failure.

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# **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A = 25^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Value	Unit
T <sub>STG</sub>	Storage Temperature	-55 to +150	°C
T <sub>OPR</sub>	Operating Temperature	-55 to +100	°C
Т <sub>Ј</sub>	Junction Temperature	-55 to +125	°C
T <sub>SOL</sub>	Lead Solder Temperature	260 for 10 sec- onds	°C
Р	Total Device Power Dissipation @ T <sub>A</sub> = 25°C	400	mW
PD	Derate Above 25°C	5.33	mW/°C
EMITTER (Eac	h channel)		
١ <sub>F</sub>	DC / Average Forward Input Current	60	mA
l <sub>F</sub> (pk)	Forward Current - Peak (PW = 1µs, 300pps)	3	А
V <sub>R</sub>	Reverse Input Voltage	3	V
P	Total Power Dissipation @ T <sub>A</sub> = 25°C	100	mW
P <sub>D(EMITTER)</sub>	Derate Above 25°C	1.3	mW/°C
DETECTOR			
Ι <sub>C</sub>	Continuous Collector Current	30	mA
D	Total Power Dissipation @ T <sub>A</sub> = 25°C	150	mW
P <sub>D(DETECTOR)</sub>	Derate Above 25°C	2.0	mW/°C

# **Electrical Characteristics**

 $T_A$  = 25°C unless otherwise specified.

Individual Component Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
EMITTER						
V <sub>F</sub>	Input Forward Voltage	I <sub>F</sub> = 20 mA		1.2	1.5	V
V <sub>R</sub>	Reverse Voltage	I <sub>R</sub> = 10 μA	3	25		V
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 5 V		0.001	10	μA
CJ	Junction Capacitance	V <sub>F</sub> = 0 V, f = 1 MHz		50		pF
DETECTO	DR		•	•		
BV <sub>CEO</sub>	Collector-to-Emitter Breakdown Voltage	I <sub>C</sub> = 1.0 mA, I <sub>F</sub> = 0	30	85		V
BV <sub>ECO</sub>	Emitter-to-Collector Breakdown Voltage	I <sub>E</sub> = 100 μA, I <sub>F</sub> = 0	6	13		V
I <sub>CEO</sub>	Collector-to-Emitter Dark Current	V <sub>CE</sub> = 10 V, I <sub>F</sub> = 0		5	100	nA
C <sub>CE</sub>	Capacitance	V <sub>CE</sub> = 0 V, f = 1 MHz		8		pF

### **Transfer Characteristics**

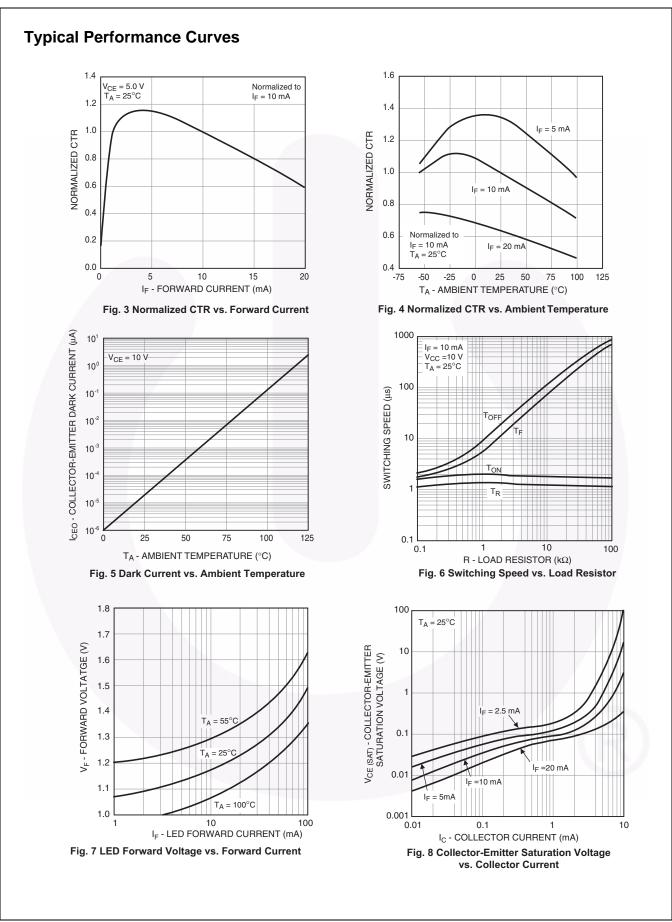
Symbol	Parameter	Device	Test Conditions	Min.	Тур.	Max.	Unit
DC CHAR	DC CHARACTERISTICS						
	CTR Current Transfer Ratio, Collector-	MCT6	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 10 V	20			
CTR		MCT61	$L = E m A \lambda ( = E \lambda ($	50			%
			– I <sub>F</sub> = 5 mA, V <sub>CE</sub> = 5 V	100			
VCE <sub>(SAT)</sub>	Saturation Voltage, Collector-to- Emitter	ALL	I <sub>F</sub> = 16 mA, I <sub>C</sub> = 2 mA		0.15	0.4	V

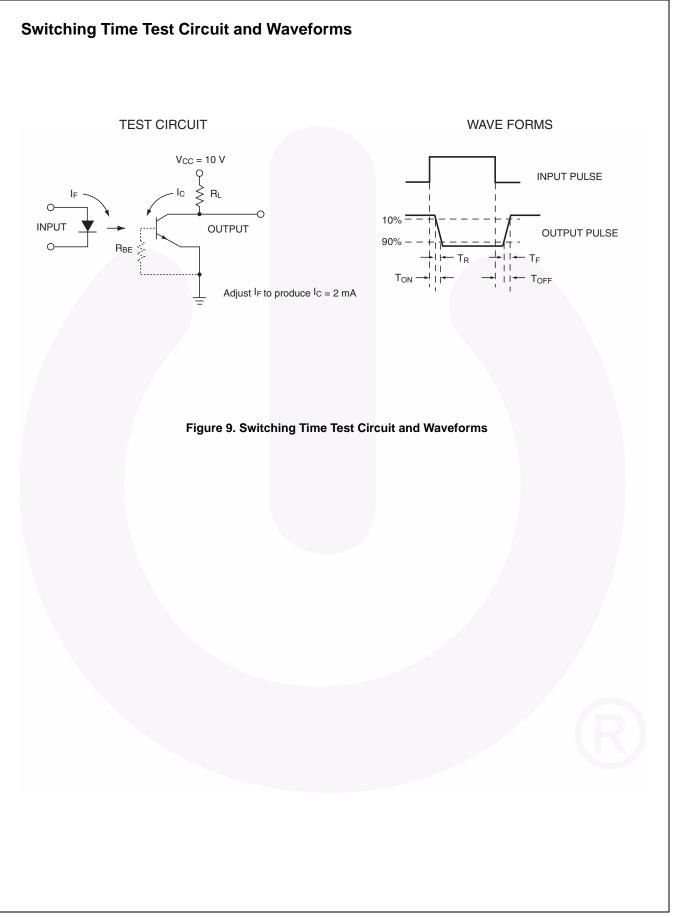
### AC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Non-Satu	rated	·		•		
T <sub>ON</sub>	Turn-On Time			3.0		μs
T <sub>OFF</sub>	Turn-Off Time			3.0		μs
T <sub>R</sub>	Rise Time	$-R_{\rm L} = 100 \ \Omega, \ I_{\rm C} = 2 \ \text{mA}, \ V_{\rm CC} = 10 \ \text{V}$		2.4		μs
Τ <sub>F</sub>	Fall Time	1 [		2.4		μs
Saturated	I			3		
T <sub>ON</sub>	Turn-On Time	I <sub>F</sub> = 16 mA, R <sub>I</sub> = 1.9 kΩ, V <sub>CF</sub> = 5 V		2.4		μs
T <sub>OFF</sub>	Turn-Off Time	$-1_{\rm F} = 10  {\rm mA},  {\rm R}_{\rm L} = 1.9  {\rm R}_{\rm Z},  {\rm v}_{\rm CE} = 5  {\rm v}$		25.0		μs

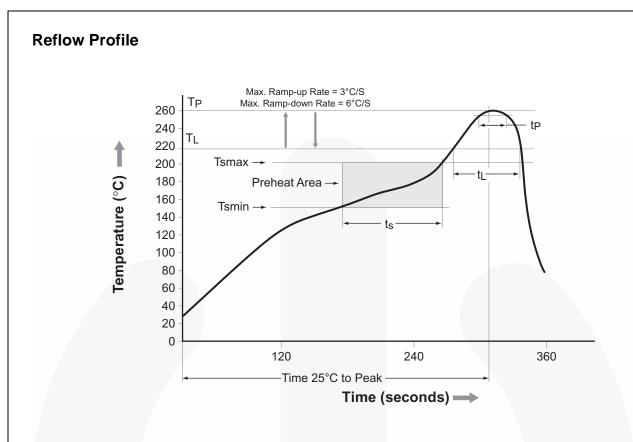
### **Isolation Characteristics**

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>ISO</sub>	Input-Output Isolation Voltage	$I_{I-O} \le 10 \ \mu A, t = 1 \ Minute$	5,000			$\rm VAC_{RMS}$
C <sub>ISO</sub>	Isolation Capacitance	f = 1 MHz		0.5		pF
R <sub>ISO</sub>	Isolation Resistance	V <sub>I-O</sub> = 500 VDC	10 <sup>11</sup>			Ω





MCT6, MCT61, MCT62 8-Pin Dual Channel Phototransistor Optocouplers



Pb-Free Assembly Profile		
150°C		
200°C		
60–120 seconds		
3°C/second max.		
217°C		
60–150 seconds		
260°C +0°C / –5°C		
30 seconds		
6°C/second max.		
8 minutes max.		

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# **Ordering Information**

Part Number	Package	Packing Method
MCT6	DIP 8-Pin	Tube (50 units per tube)
MCT6S	SMT 8-Pin (Lead Bend)	Tube (50 units per tube)
MCT6SD	SMT 8-Pin	Tape and Reel (1,000 units per reel)
MCT6300	DIN EN/IEC 60747-5-5 Option	Tube (50 units per tube)
MCT63S	SMT 8-Pin (Lead Bend); DIN EN/IEC 60747-5-5 Option	Tube (50 units per tube)
MCT63SD	SMT 8-Pin; DIN EN/IEC 60747-5-5 Option	Tape and Reel (1,000 units per reel)
MCT6300W	0.4" Lead Spacing; DIN EN/IEC 60747-5-5 Option	Tube (50 units per tube)

### Note

1. The product orderable part number system listed in this table also applies to the MCT61 and MCT62.

# Marking Information

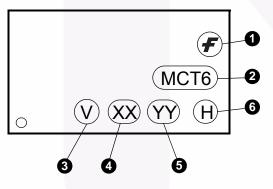
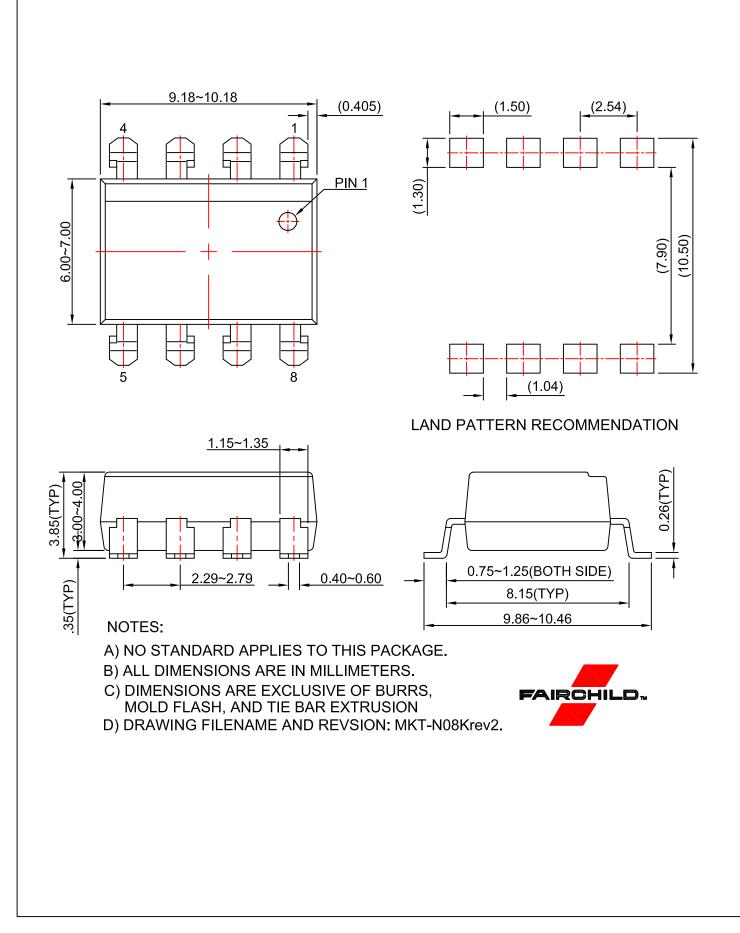
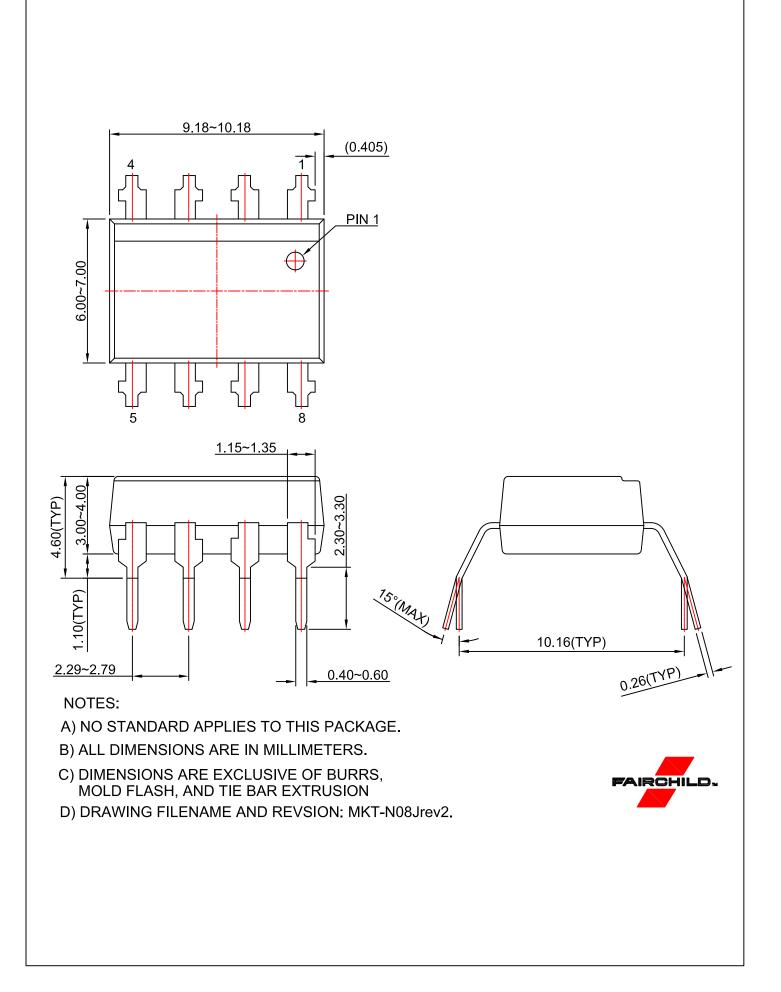


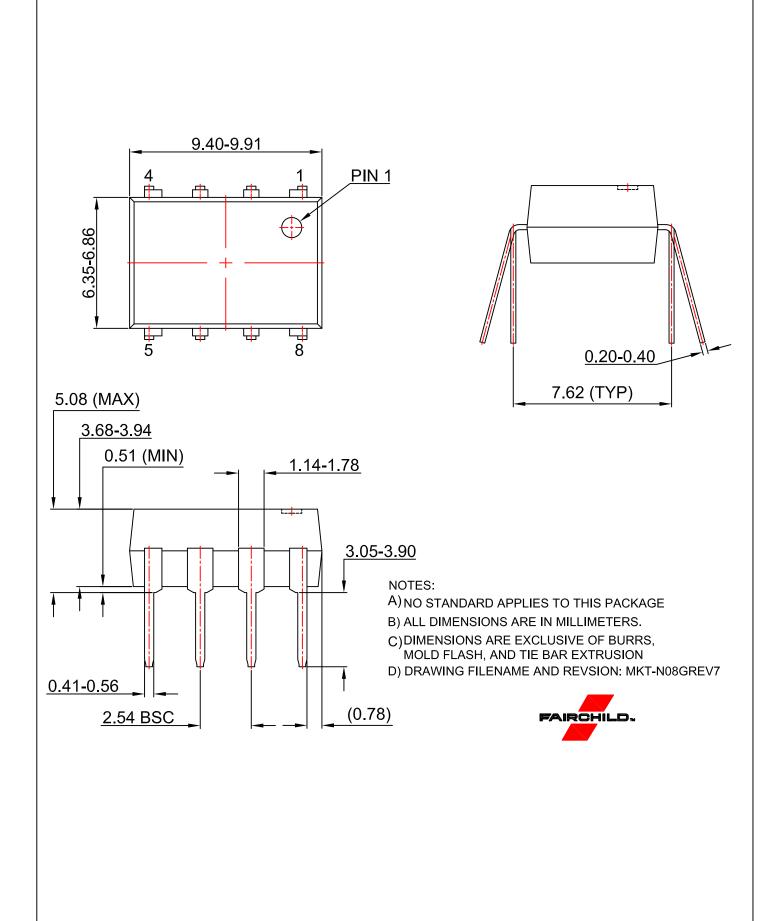
Figure 10. Top Mark

### **Table 1. Top Mark Definitions**

1	Fairchild Logo	
2	Device Number	
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)	
4	Two-Digit Year Code, e.g., "16"	
5	Digit Work Week, Ranging from "01" to "53"	
6	Assembly Package Code	









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